2822

PATENT #11B 3-31-03

Attorney Docket No. 5649-877

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Hag-ju Cho et al.
Serial No.: 09/923,670
Filed: August 7, 2001
For: METHODS OF FABRICATING INTEGRATED CIRCUIT DEVICES HAVING DIELECTRIC REGIONS PROTECTED WITH MULTI-LAYER INSULATION STRUCTURES (AS AMENDED)

Group Art Unit: 2822
Examiner: Toniae M. Thomas

DATE: March 17, 2003



BOX NON-FEE AMENDMENT
Commissioner for Patents
Washington, DC 20231

**AMENDMENT**

Sir:

This Amendment is responsive to the Office Action of December 26, 2002. The claims have been amended herein using the rewritten paragraphs and claims format. The present amendment also includes a section entitled "**VERSION WITH MARKINGS TO SHOW CHANGES MADE**" attached hereto.

It is not believed that an extension of time and/or additional fee(s), including fees for additional claims, are required, beyond those that may otherwise be provided for in documents accompanying this paper. In the event, however, that an extension of time is necessary to allow consideration of this paper, such an extension is hereby petitioned under 37 C.F.R. §1.136(a). Any additional fees believed to be due in connection with this paper may be charged to our Deposit Account No. 50-0220.

**In the Specification:**

Please replace the paragraph beginning at page 3, line 15, with the following rewritten paragraph:

-- In still other embodiments of the present invention, an integrated circuit comprises a ferroelectric dielectric region on a substrate, a first metal oxide layer directly on a surface of the ferroelectric dielectric region, and a second metal oxide layer on the first metal oxide layer. The first metal oxide layer is configured to enable a remnant polarization of the ferroelectric dielectric region to increase during an annealing of the substrate before formation of the second metal oxide layer. The first